Broadband Low Noise Gain Block, Die, 16 dB 0.03 - 8 GHz



MAAM-011305-DIE Rev. V3

Features

- 16 dB Flat Broadband Gain to 8 GHz
- · Low Noise Figure:
 - 1.6 dB Noise Figure to 1.5 GHz
 - 2.5 dB Noise Figure @ 6 GHz
 - 3.6 dB Noise Figure @ 8 GHz
- High Linearity OIP3:
 - 38 dBm @ 1.5 GHz
 - 32 dBm @ 6 GHz
 - 27 dBm @ 8 GHz
- Internal Matching to 50 Ω
- Single Voltage Bias: 3 5 V
- Integrated Active Bias Circuit
- RoHS* Compliant

Applications

• ISM/MM

Description

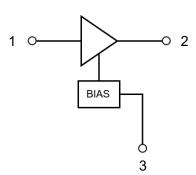
The MAAM-011305-DIE is a broadband high dynamic range, single stage MMIC LNA. This bare die is 0.795 x 0.66 mm. The amplifier is internally matched to provide flat gain and good return losses to 8 GHz without any external matching components. Only DC blocking capacitors and an RF choke with bypass capacitance is required.

This low noise amplifier has an integrated active bias circuit allowing direct connection to 3 V or 5 V bias and minimizing variations over temperature and process.

Ordering Information

Part Number	Package
MAAM-011305-DIEPPR	Bare Die

Functional Block Diagram



Pin Configuration¹

Pin#	Pin Name	Description	
1	RF _{IN}	RF Input	
2	RF _{OUT} /V _{DD}	RF Output / Drain Voltage	
3	NC	No Connection	

1. Bottom of die is RF and thermal ground.

^{*} Restrictions on Hazardous Substances, compliant to current RoHS EU directive.



Electrical Specifications: $V_{DD} = 5 \text{ V}$, +25°C, $Z_0 = 50 \Omega$ (all data is GSG probed)

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Gain	0.03 - 8 GHz	dB	14	16	_
Noise Figure	0.1 - 1.5 GHz 6.0 GHz 8.0 GHz	dB	_	1.6 2.5 3.6	_
Input Return Loss	0.03 - 8 GHz	dB		10	_
Output Return Loss	0.03 - 8 GHz	dB	_	10	_
Output IP3	P _{IN} = -15 dBm per tone, 6 MHz spacing 0.03 - 3 GHz 6 GHz 8 GHz	dBm	_	37 32 27	_
Output IP2	P _{IN} = -15 dBm per tone, 6 MHz spacing 0.03 - 3 GHz 6 GHz 8 GHz	dBm	_	44 50 52	_
Output P1dB	0.03 - 3 GHz 6 GHz 8 GHz	dBm	-	20 18 14	_
Current	I _{DD}	mA	_	66	85

Maximum Operating Ratings

Parameter	Maximum	
RF Input Power CW	10 dBm	
V _{DD}	6 V	
I _{DQ}	100 mA	
Operating Temperature	-40°C to +85°C	
Junction Temperature ^{4,5}	+160°C	

- 2. Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.
- 4. Operating at nominal conditions with $T_J \le 160^{\circ}$ C will ensure MTTF > 1 x 10^{6} hours.
- 5. Junction Temperature (T_J) = T_C + Θ_{JC} * ((V * I) (P_{OUT} P_{IN})) Typical thermal resistance (Θ_{JC}) = 40°C/W
 - a) For T_C = 25°C,

T_J = 39°C @ 5 V, 66 mA

b) For $T_C = 85^{\circ}C$,

 $T_J = 100^{\circ}C @ 5 V, 75 mA$

Absolute Maximum Ratings^{2,3}

Parameter	Absolute Maximum	
RF Input Power CW	24 dBm	
V _{DD}	7 V	
Storage Temperature	-55°C to +150°C	

Handling Procedures

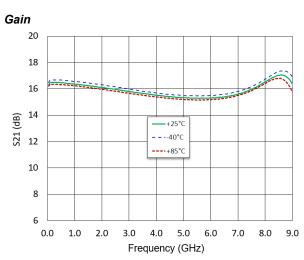
Please observe the following precautions to avoid damage:

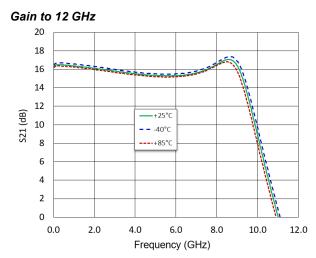
Static Sensitivity

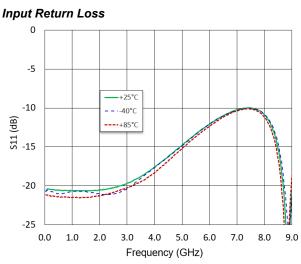
Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1C devices.

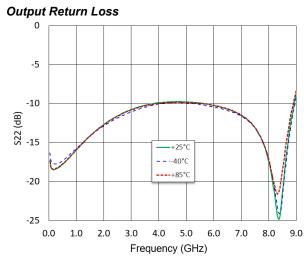


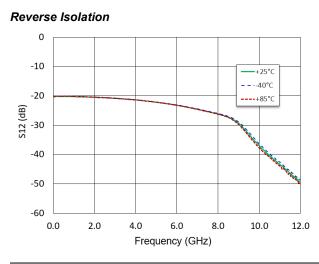
Typical Performance Curves @ 5 V / 66 mA, $Z_0 = 50 \Omega$ (all data is GSG probed)

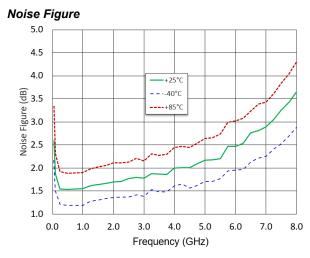












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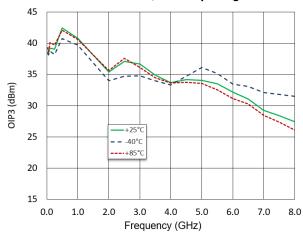
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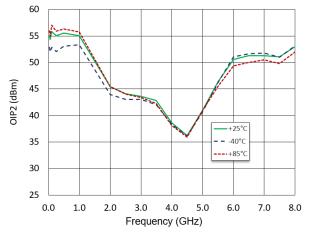


Typical Performance Curves @ 5 V / 66 mA, $Z_0 = 50 \Omega$ (all data is GSG probed)

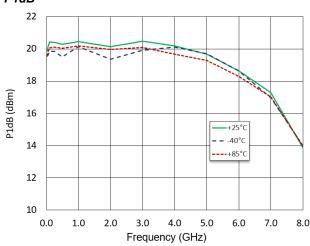
OIP3 at P_{IN} = -15 dBm/tone, 6MHz Spacing



OIP2 at P_{IN} = -15 dBm/tone, 6MHz Spacing

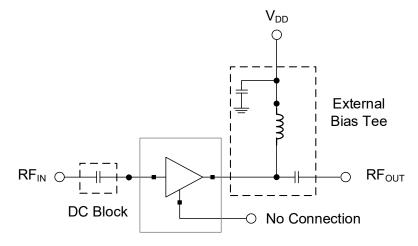


P1dB

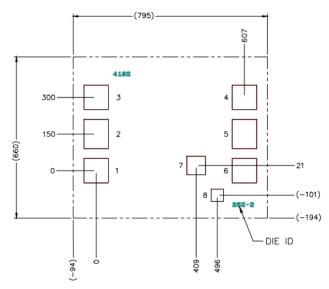




Typical Application Circuit



Die Outline^{6,7,8,9,10} (0.795 x 0.660 mm)



Bond Pad Dimensions (µm)

Pad #	Size (x)	Size (y)	Description
1, 3, 6, 8	100	100	GND
2	100	120	RF _{IN}
7	100	120	RF _{OUT} / V _{DD}
4	76	76	No Connection
5	50	50	GND

- 6. Unless otherwise specified, all dimensions shown are μm with a tolerance of $\pm 5~\mu m$.
- 7. Die thickness is 100 ±10 µm.
- 8. Bond pad/backside metallization: Gold.
- 9. Die size reflects cut dimensions. Saw or laser kerf reduces die size ~22 µm each dimension
- 10. GND bond pads 1, 3, 5, 6 and 8 are connected to the backside of the die through via holes. GND bond pads do not require bond wires, only pin 2 and 7 require bond wires.

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